2SK1637, 2SK2422

Silicon N-Channel MOS FET

HITACHI

ADE-208-1305 (Z) 1st. Edition Mar. 2001

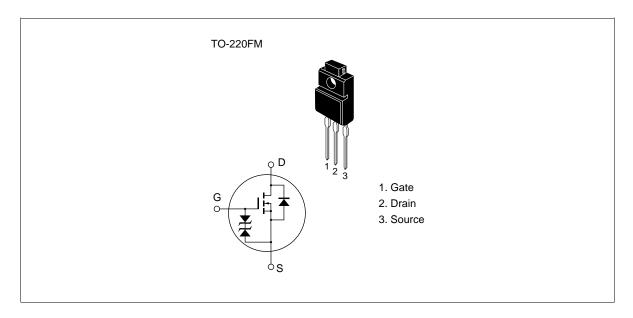
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- · No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline





2SK1637, 2SK2422

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1637	$V_{ t DSS}$	600	V
	2SK2422		650	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I _D	4	А
Drain peak current		l *1 D(pulse)	16	A
Body to drain diode reverse drain current		I _{DR}	4	A
Channel dissipation		Pch*2	35	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

Note

^{1.} PW 10 µs, duty cycle 1%

^{2.} Value at $T_c = 25$ °C

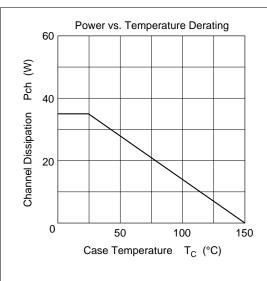
Electrical Characteristics ($Ta = 25^{\circ}C$)

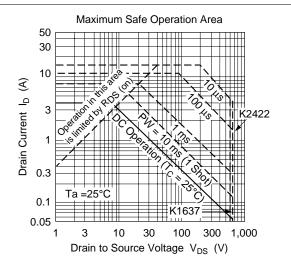
Item		Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source 2	2SK1637	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
breakdown voltage 2	2SK2422	-	650	_			
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current		I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage 2	2SK1637	I _{DSS}	_	_	250	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
drain current 2	2SK2422	-					$V_{DS} = 550 \text{ V}, V_{GS} = 0$
Gate to source cutoff vo	oltage	$V_{GS(off)}$	2.0		3.0	V	$I_{D} = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source 2	2SK1637	R _{DS(on)}	_	1.8	2.4		$I_D = 2 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
on state resistance	2SK2422	-	_	2.0	2.6		
Forward transfer admittance		yfs	2.2	3.5	_	S	$I_D = 2 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance		Ciss	_	600	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance		Coss	_	140	_	pF	f = 1 MHz
Reverse transfer capac	itance	Crss	_	25	_	pF	_
Turn-on delay time		t _{d(on)}	_	8	_	ns	$I_D = 2 A, V_{GS} = 10 V,$
Rise time		t _r	_	30	_	ns	R _L = 15
Turn-off delay time		$t_{d(off)}$	_	60	_	ns	_
Fall time		t _f	_	35	_	ns	_
Body to drain diode for voltage	ward	V_{DF}	_	0.9	_	V	$I_F = 4 A, V_{GS} = 0$
Body to drain diode reverse recovery time		t _{rr}	_	300	_	ns	$I_F = 4 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A/}\mu\text{s}$

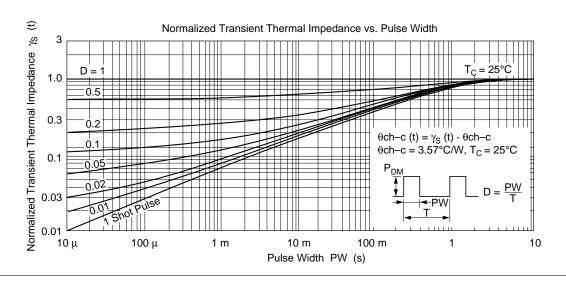
Note 1. Pulse test

See characteristics curves of 2SK1402, 2SK1402A.

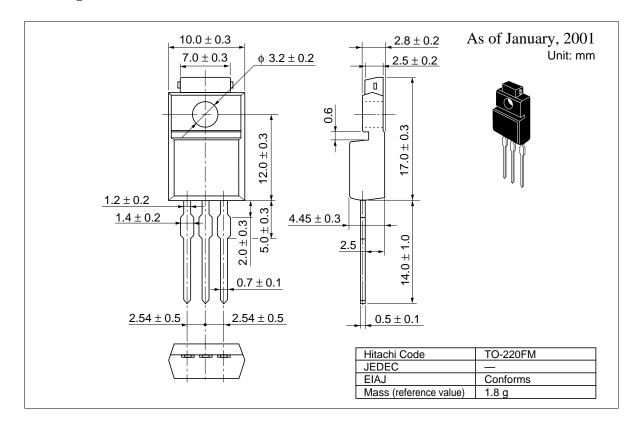
2SK1637, 2SK2422







Package Dimensions



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